IN THE CLAIMS:

1. (Currently Amended) A method of manufacturing a semiconductor wafer, comprising the steps of:

annealing a wafer at a low temperature under nitrogen (N_2) atmosphere in order to form a nucleation site at a region deep into the wafer; and

performing a rapid thermal annealing process under nitrogen (N_2) atmosphere after forming the nucleation site so that oxygen precipitation material[[,]] or metallic impurity~~, etc.~~ is trapped in the nucleation site.

2. (Currently Amended) The method as claimed in claim 1, wherein the low-temperature annealing process is performed at a temperature of 650 ~ 850°C ~~under nitrogen (N_2) atmosphere~~ for 3 ~ 10 hours.

3 (Currently Amended) The method as claimed in claim 1, wherein the rapid thermal annealing process is performed at a temperature of 1000 ~ 1200°C ~~under nitrogen (N_2) atmosphere~~ for 10 seconds ~ 5 minutes.

4 (Original) The method as claimed in claim 1, wherein in the rapid thermal annealing process, a step-up rate is 30 ~ 200°C/sec, a cooling rate is 200 ~ 100°C/sec and the flux of nitrogen (N_2) is 1 ~ 20slpm.

5 (Original) The method as claimed in claim 1, further comprising the step of before the low-temperature annealing process is implemented, performing high-temperature annealing process in order to diffuse oxygen existing on the surface of the wafer toward the outside.

6. (Currently Amended) The method as claimed in claim 5, wherein the ~~low~~high-temperature annealing process is performed at a temperature of 1000 ~ 1200°C under dry oxygen (O_2) atmosphere for 1 ~ 2 hours.